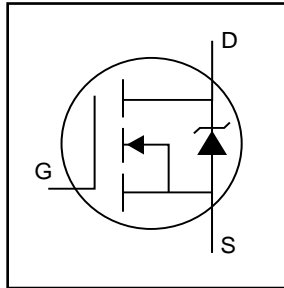


IRL2203S

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Surface Mount
- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



$$V_{DSS} = 30V$$

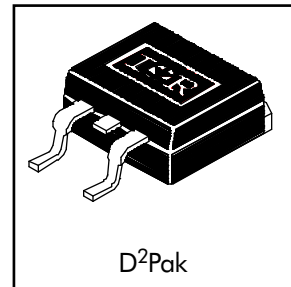
$$R_{DS(on)} = 0.007\Omega$$

$$I_D = 100A\text{⑤}$$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V⑥	100⑤	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V⑥	71	
I_{DM}	Pulsed Drain Current ①⑥	400	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	130	W
	Linear Derating Factor	0.83	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②⑥	390	mJ
I_{AR}	Avalanche Current ①	60	A
E_{AR}	Repetitive Avalanche Energy ①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑥	1.2	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

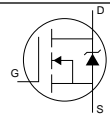
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	—	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/°C	Reference to 25°C, I _D = 1mA ^⑥
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.007		V _{GS} = 10V, I _D = 60A ^④
		—	—	0.01		V _{GS} = 4.5V, I _D = 50A ^④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	47	—	—	S	V _{DS} = 25V, I _D = 60A ^⑥
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 30V, V _{GS} = 0V
		—	—	250		V _{DS} = 24V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	110	nC	I _D = 60A
Q _{gs}	Gate-to-Source Charge	—	—	31		V _{DS} = 24V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	57		V _{GS} = 4.5V, See Fig. 6 and 13 ^{④⑥}
t _{d(on)}	Turn-On Delay Time	—	15	—		V _{DD} = 15V
t _r	Rise Time	—	210	—	ns	I _D = 60A
t _{d(off)}	Turn-Off Delay Time	—	29	—		R _G = 1.8Ω, V _{GS} = 4.5V
t _f	Fall Time	—	54	—		R _D = 0.25Ω, See Fig. 10 ^{④⑥}
L _S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C _{iss}	Input Capacitance	—	3500	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1400	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	690	—		f = 1.0MHz, See Fig. 5 ^⑥

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	100 ^⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ^①	—	—	400		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 60A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	94	140	ns	T _J = 25°C, I _F = 60A
Q _{rr}	Reverse Recovery Charge	—	280	410	nC	di/dt = 100A/μs ^{④⑥}



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 15V, starting T_J = 25°C, L = 220μH
R_G = 25Ω, I_{AS} = 60A. (See Figure 12)
- ③ I_{SD} ≤ 60A, di/dt ≤ 140A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4
- ⑥ Uses IRL2203N data and test conditions.

** When mounted on FR-4 board using minimum recommended footprint.
For recommended footprint and soldering techniques refer to application note #AN-994.

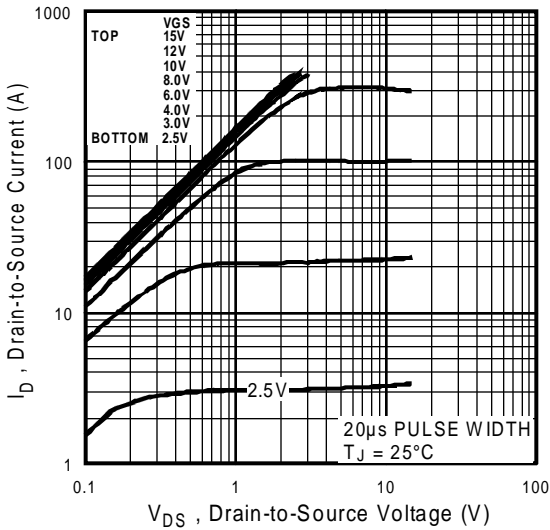


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ C$

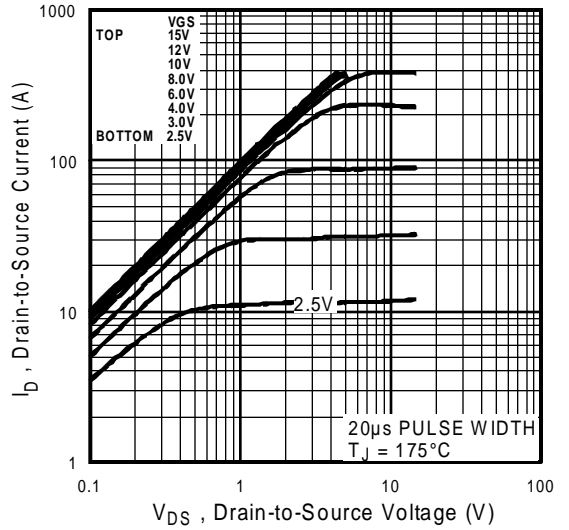


Fig 2. Typical Output Characteristics,
 $T_J = 175^\circ C$

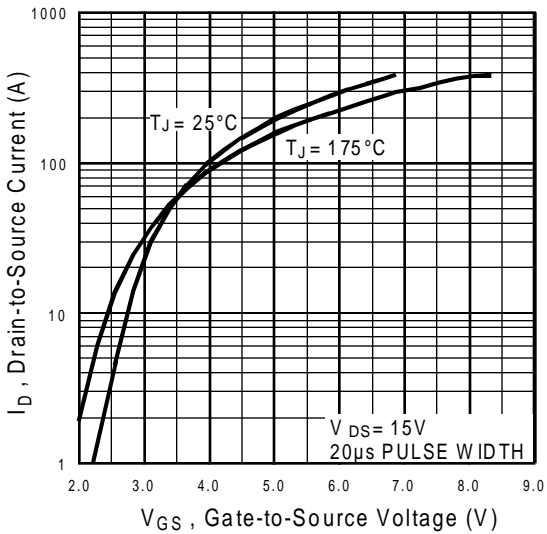


Fig 3. Typical Transfer Characteristics

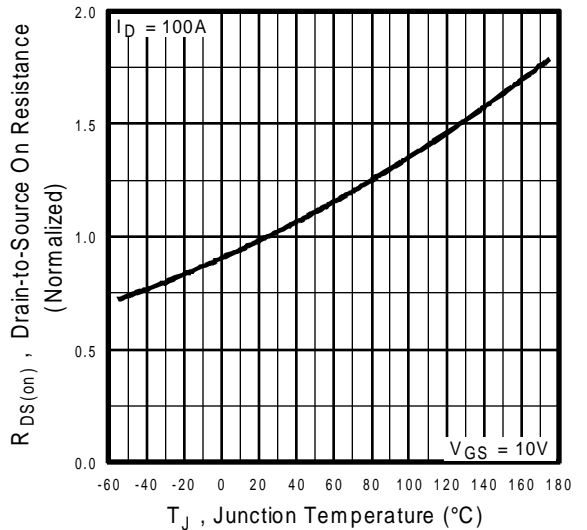


Fig 4. Normalized On-Resistance
Vs. Temperature

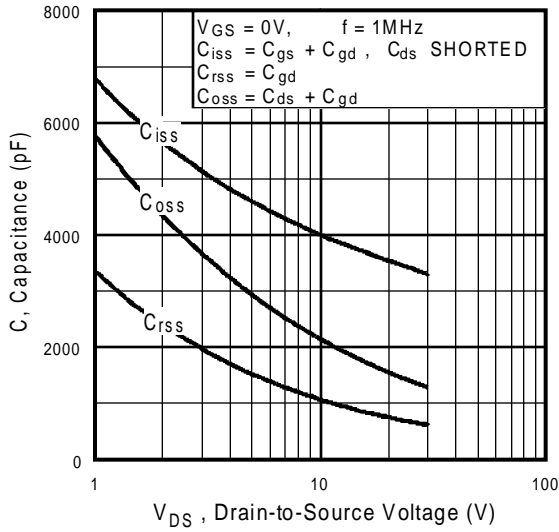


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

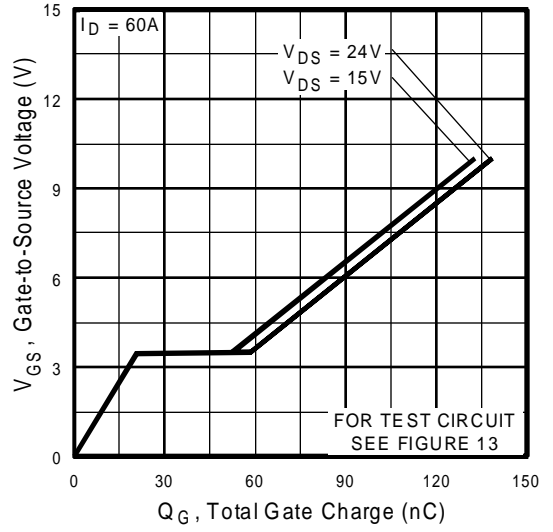


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

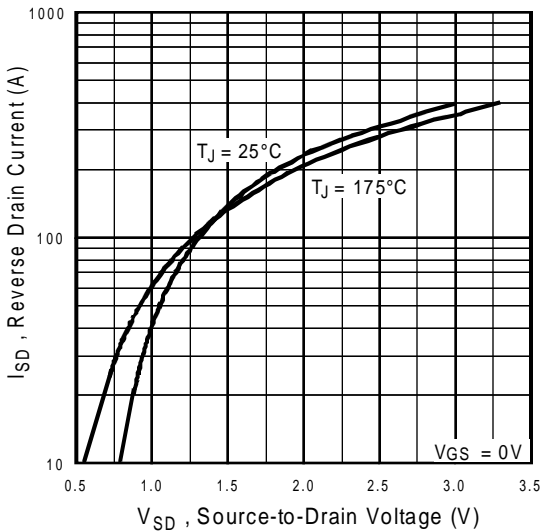


Fig 7. Typical Source-Drain Diode Forward Voltage

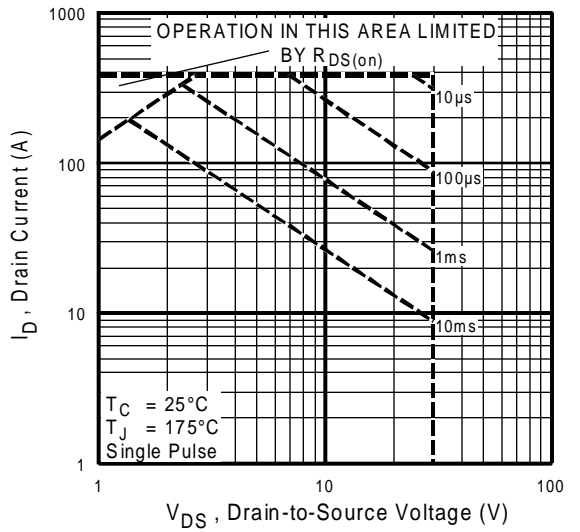


Fig 8. Maximum Safe Operating Area

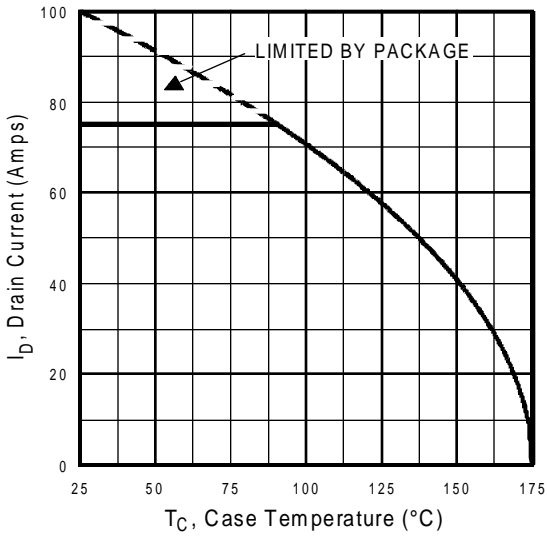


Fig 9. Maximum Drain Current Vs. Case Temperature

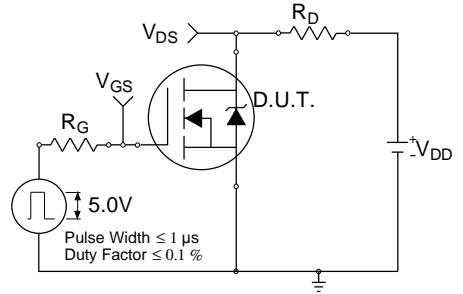


Fig 10a. Switching Time Test Circuit

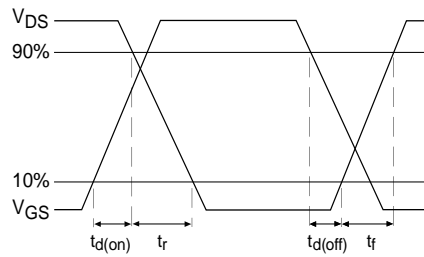


Fig 10b. Switching Time Waveforms

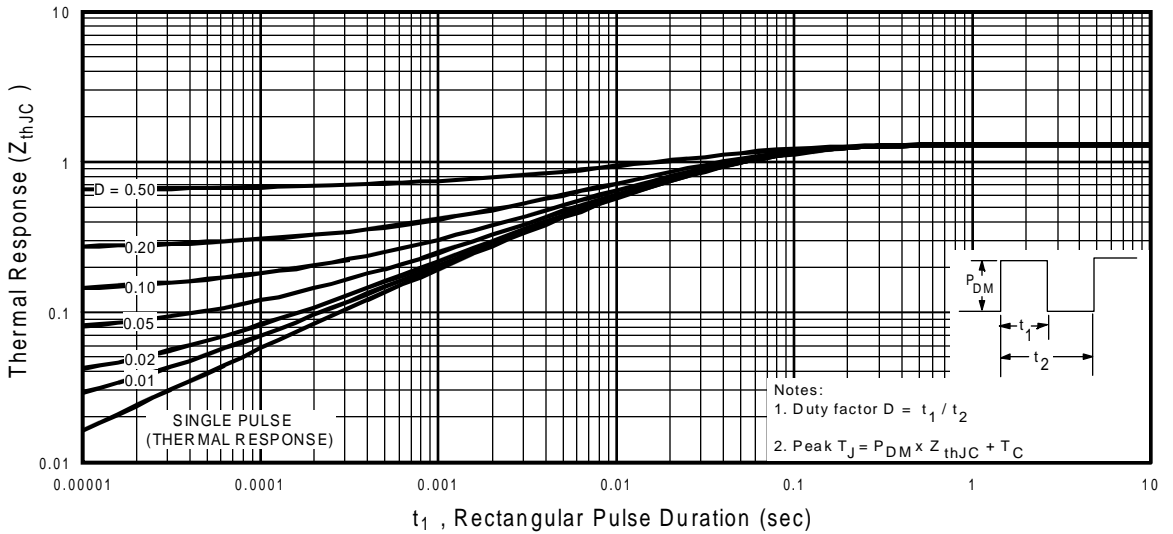


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

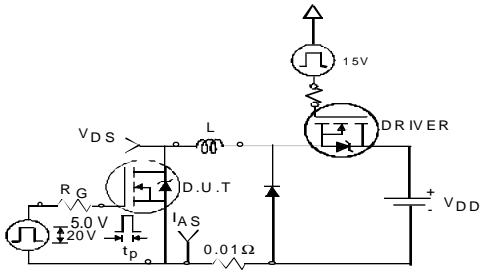


Fig 12a. Unclamped Inductive Test Circuit

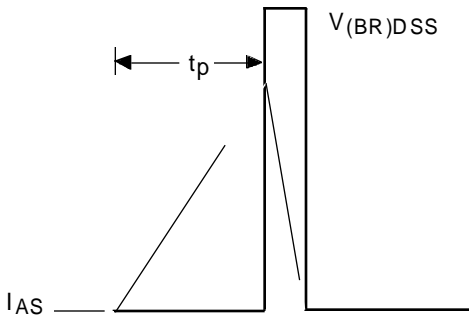


Fig 12b. Unclamped Inductive Waveforms

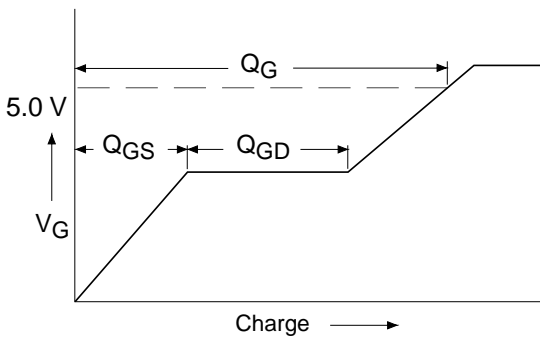


Fig 13a. Basic Gate Charge Waveform

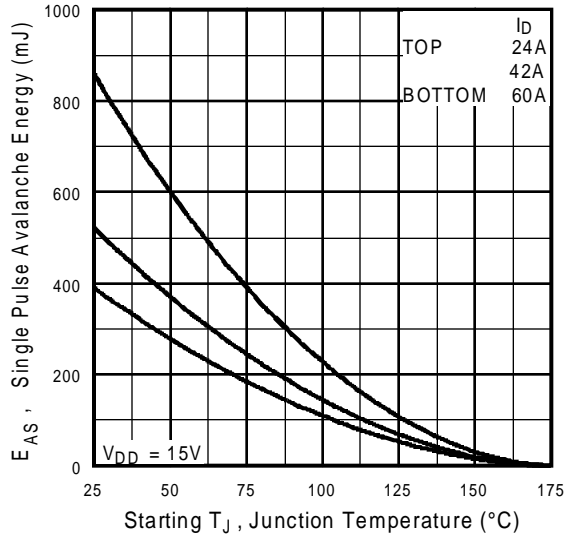


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

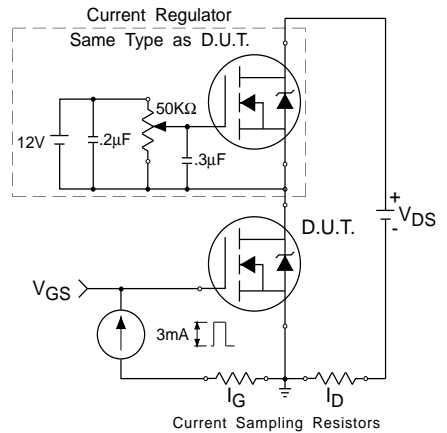
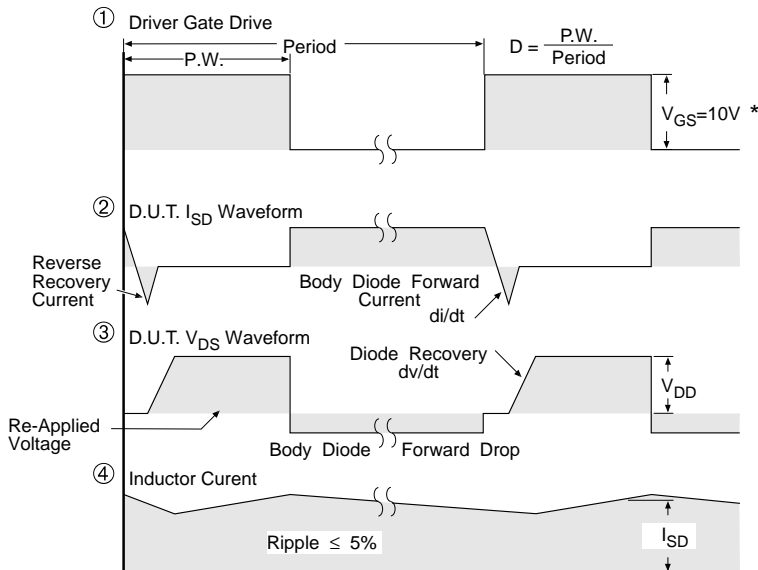
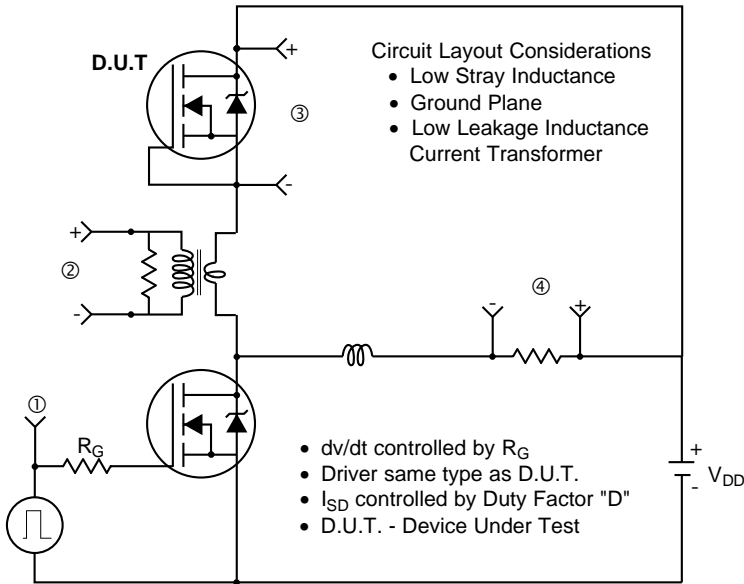


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



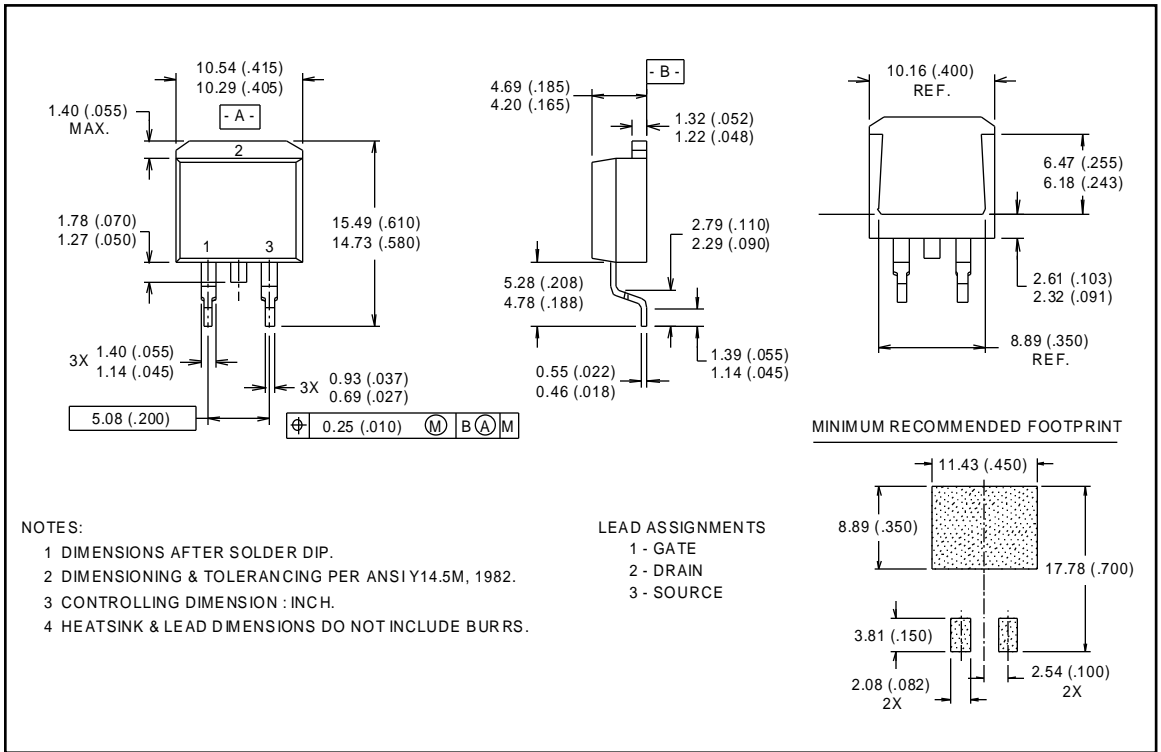
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

IRL2203S

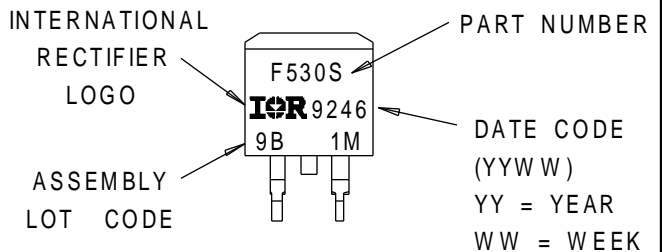
Package Outline — D²Pak

Dimensions are shown in millimeters (inches)



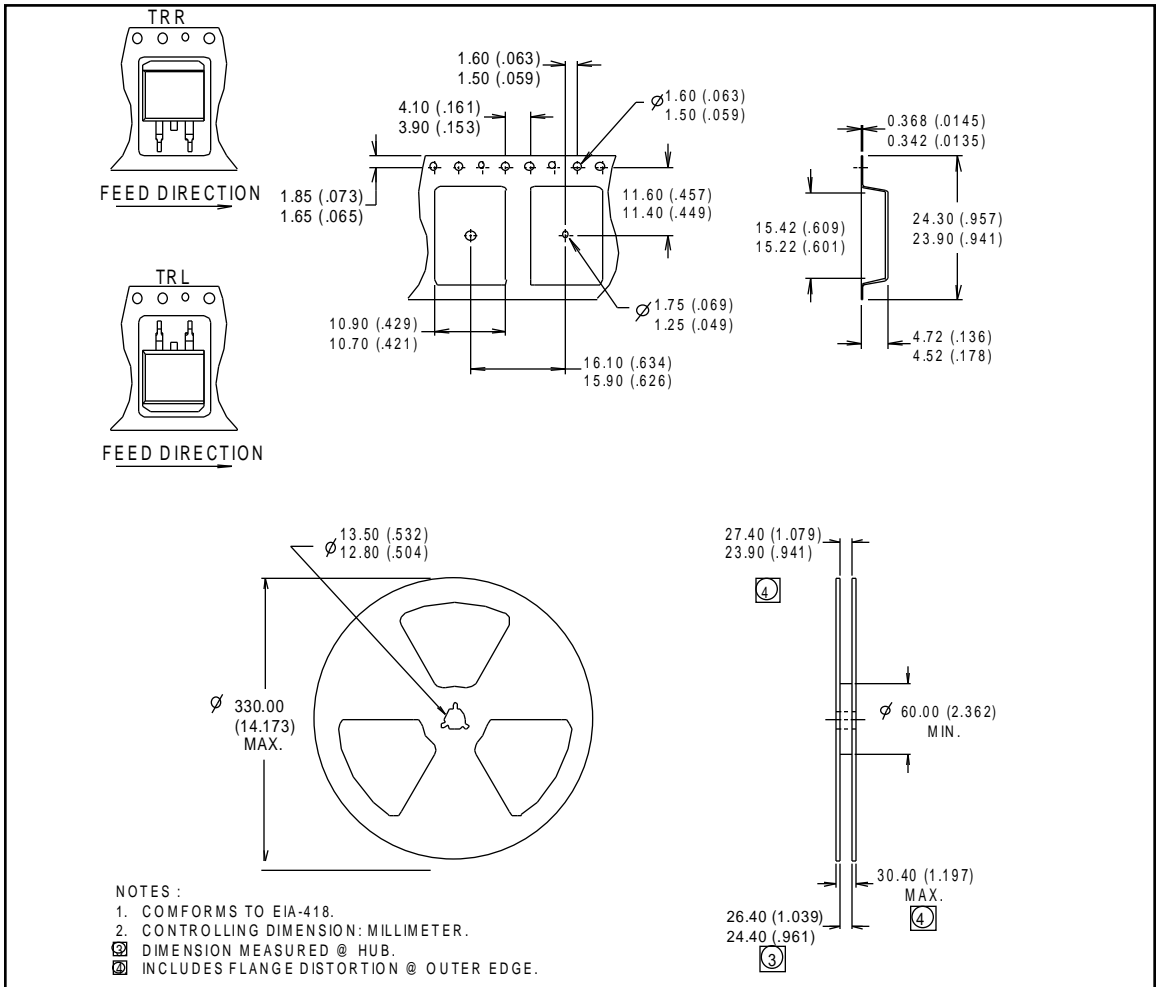
Part Marking

EXAMPLE : THIS IS AN IRF530S
WITH ASSEMBLY
LOT CODE 9B1M



Tape & Reel — D²Pak

Dimensions are shown in millimeters (inches)



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EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

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